

Kanako Shojiki

List of Publications by Year in descending order

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38
times ranked

494
citing authors

#	ARTICLE	IF	CITATIONS
1	Reduction of threading dislocation density and suppression of cracking in sputter-deposited AlN templates annealed at high temperatures. Applied Physics Express, 2019, 12, 065501.	1.1	59
2	Red to blue wavelength emission of N-polar InGaIn light-emitting diodes grown by metalorganic vapor phase epitaxy. Applied Physics Express, 2015, 8, 061005.	1.1	49
3	Suppression of dislocation-induced spiral hillocks in MOVPE-grown AlGaIn on face-to-face annealed sputter-deposited AlN template. Applied Physics Letters, 2020, 116, .	1.5	44
4	Toward Bright and Pure Single Photon Emitters at 300 K Based on GaN Quantum Dots on Silicon. ACS Photonics, 2020, 7, 1515-1522.	3.2	36
5	Quantitative evaluation of strain relaxation in annealed sputter-deposited AlN film. Journal of Crystal Growth, 2019, 512, 16-19.	0.7	27
6	Annealing behaviors of vacancy-type defects in AlN deposited by radio-frequency sputtering and metalorganic vapor phase epitaxy studied using monoenergetic positron beams. Journal of Applied Physics, 2020, 128, .	1.1	24
7	Improvement of surface morphology of nitrogen-polar GaN by introducing indium surfactant during MOVPE growth. Japanese Journal of Applied Physics, 2014, 53, 085501.	0.8	22
8	263 nm wavelength UV-C LED on face-to-face annealed sputter-deposited AlN with low screw- and mixed-type dislocation densities. Applied Physics Express, 2022, 15, 055501.	1.1	21
9	Impact of face-to-face annealed sputtered AlN on the optical properties of AlGaIn multiple quantum wells. AIP Advances, 2019, 9, 125342.	0.6	18
10	MOVPE growth of AlN films on nano-patterned sapphire substrates with annealed sputtered AlN. Journal of Crystal Growth, 2020, 532, 125397.	0.7	17
11	Enhancement of surface migration by Mg doping in the metalorganic vapor phase epitaxy of N-polar GaN/sapphire. Japanese Journal of Applied Physics, 2014, 53, 05FL05.	0.8	16
12	High-Quality AlN Template Prepared by Face-to-Face Annealing of Sputtered AlN on Sapphire. Physica Status Solidi (B): Basic Research, 2021, 258, 2000352.	0.7	16
13	Preparation of high-quality thick AlN layer on nanopatterned sapphire substrates with sputter-deposited annealed AlN film by hydride vapor-phase epitaxy. Japanese Journal of Applied Physics, 2019, 58, SC1003.	0.8	15
14	Quantification of scattering loss of III-nitride photonic crystal cavities in the blue spectral range. Physical Review B, 2017, 95, .	1.1	14
15	Homogeneity improvement of N-polar InGaIn /GaN multiple quantum wells by using c-plane sapphire substrate with off-cut-angle towards sapphire plane. Japanese Journal of Applied Physics, 2016, 55, 05FA09.	0.8	13
16	Fabrication of AlN templates on SiC substrates by sputtering-deposition and high-temperature annealing. Journal of Crystal Growth, 2019, 510, 13-17.	0.7	12
17	Reduction of threading dislocation densities of N-polar face-to-face annealed sputtered AlN on sapphire. Journal of Crystal Growth, 2021, 574, 126309.	0.7	12
18	Local and anisotropic strain in AlN film on sapphire observed by Raman scattering spectroscopy. Japanese Journal of Applied Physics, 2019, 58, SCCB17.	0.8	11

#	ARTICLE	IF	CITATIONS
19	Crystalline quality improvement of face-to-face annealed MOVPE-grown AlN on vicinal sapphire substrate with sputtered nucleation layer. Journal of Crystal Growth, 2020, 545, 125722.	0.7	10
20	Curvature-controllable and crack-free AlN/sapphire templates fabricated by sputtering and high-temperature annealing. Journal of Crystal Growth, 2019, 512, 131-135.	0.7	9
21	Centimeter-scale laser lift-off of an AlGaIn UVB laser diode structure grown on nano-patterned AlN. Applied Physics Express, 2022, 15, 051004.	1.1	9
22	Effect of the Sputtering Deposition Conditions on the Crystallinity of High-Temperature Annealed AlN Films. Coatings, 2021, 11, 956.	1.2	8
23	Effect of <i>c</i> -plane sapphire substrate miscut angle on indium content of MOVPE-grown N-polar InGaIn. Japanese Journal of Applied Physics, 2014, 53, 05FLO7.	0.8	7
24	Suppression of metastable-phase inclusion in N-polar (0001 \hat{A}) InGaIn/GaN multiple quantum wells grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 2015, 106, .	1.5	6
25	Nanometer scale fabrication and optical response of InGaIn/GaN quantum disks. Nanotechnology, 2016, 27, 425401.	1.3	6
26	Thick AlN layers grown on micro-scale patterned sapphire substrates with sputter-deposited annealed AlN films by hydride vapor-phase epitaxy. Journal of Crystal Growth, 2021, 566-567, 126163.	0.7	6
27	Large Stokes-like shift in N-polar $(000\hat{A})$ InGaIn/GaN multiple-quantum-well light-emitting diodes. Japanese Journal of Applied Physics, 2016, 55, 05FJ03.	0.8	5
28	Polarity control of GaIn grown on pulsed-laser-deposited AlN/GaN template by metalorganic vapor phase epitaxy. Japanese Journal of Applied Physics, 2016, 55, 05FA04.	0.8	5
29	Tilted Domain and Indium Content of InGaIn Layer on m -Plane GaIn Substrate Grown by Metalorganic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 04DH01.	0.8	3
30	Investigation of indium incorporation into InGaIn by nitridation of sapphire substrate in MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 417-420.	0.8	3
31	Effects of Mg/Ga and V/III source ratios on hole concentration of N-polar $(000\hat{A})$ p-type GaIn grown by metalorganic vapor phase epitaxy. Japanese Journal of Applied Physics, 2016, 55, 05FE01.	0.8	3
32	Thermal strain analysis considering in-plane anisotropy for sputtered AlN on <i>c</i> - and <i>a</i> -plane sapphire under high-temperature annealing. AIP Advances, 2021, 11, .	0.6	3
33	Absolute technique for measuring internal electric fields in InGaIn/GaN light-emitting diodes by electroreflectance applicable to all crystal orientations. Applied Physics Express, 2017, 10, 082101.	1.1	2
34	High-Temperature Annealing of Sputter-Deposited AlN on (001) Diamond Substrate. Physica Status Solidi (B): Basic Research, 2020, 257, 1900447.	0.7	2
35	Effect of MOVPE growth conditions on AlN films on annealed sputtered AlN templates with nano-striped patterns. Journal of Crystal Growth, 2021, 570, 126237.	0.7	2
36	Fabrication of Cu ₂ ZnSnS ₄ thin films using a Cu-Zn-Sn-O amorphous precursor and supercritical fluid sulfurization. Thin Solid Films, 2017, 638, 244-250.	0.8	1

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37	Biexciton Emission From Single Quantum-Confined Structures in N^{\ominus} -Polar (000 $\bar{1}$) InGaN/GaN Multiple Quantum Wells. <i>Physica Status Solidi (B): Basic Research</i> , 2018, 255, 1700454.	0.7	0
38	Emission color modulation of InGaN/GaN multiple quantum wells by selective area metalorganic vapor phase epitaxy on hexagonal windows. <i>Japanese Journal of Applied Physics</i> , 2022, 61, 030904.	0.8	0